## 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

### 2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R<sub>DSon</sub> in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced R<sub>th</sub> and R<sub>DSon</sub>
  - · Increases maximum current capability and improved current spreading

# 3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	190	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	395	W



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 11		0.67	0.96	1.3	mΩ
Dynamic chara	Dynamic characteristics						
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; Fig. 13; Fig. 14		-	11.2	22.4	nC
Source-drain o	Source-drain diode						
Q <sub>r</sub>	recovered charge	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C; <u>Fig. 17</u>		-	38.8	-	nC
S	softness factor			-	0.8	-	

<sup>[1] 190</sup>A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

## 5. Pinning information

#### **Table 2. Pinning information**

Table 2.1 mining information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source	mb	D			
2	s	source					
3	S	source	a J	G P			
4	G	gate		mbb076 S			
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)				

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BUK9Y1R3-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

## 7. Marking

### Table 4. Marking codes

Type number	Marking code
BUK9Y1R3-40H	91H340

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	16	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	395	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	190	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	190	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	600	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drai	n diode		'			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2]	-	145	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	600	Α
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 190 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	154	mJ

- [1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [2] 145A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}$ C.
- [4] Refer to application note AN10273 for further information.

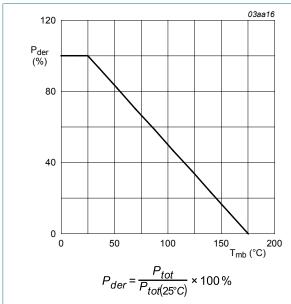
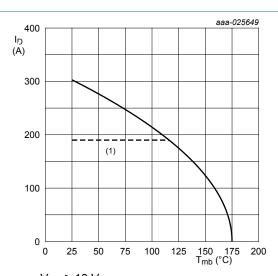


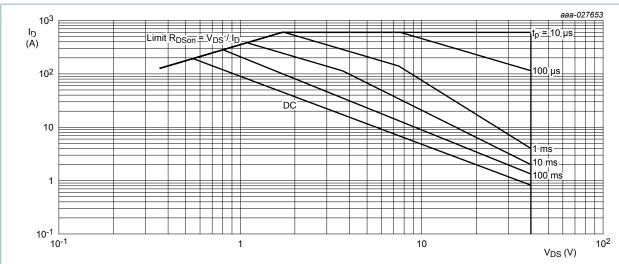
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

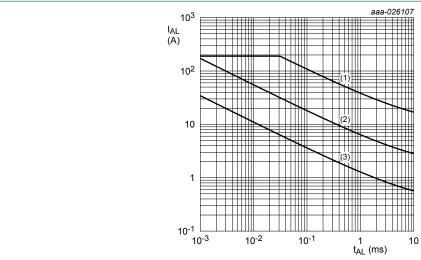
Fig. 2. Continuous drain current as a function of mounting base temperature

### N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

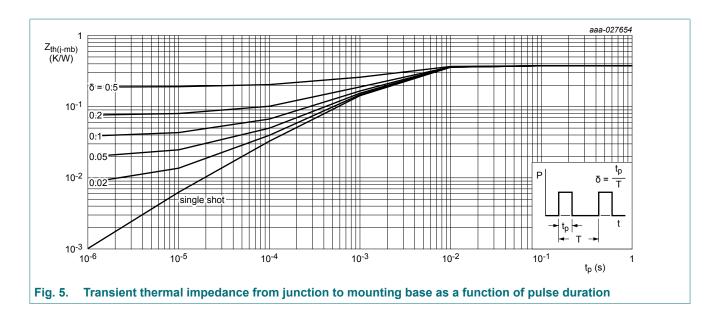
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.29	0.38	K/W

### N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	43	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.5	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u>	1.35	1.62	2.05	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10	0.6	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.4	1	μΑ
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	2.4	10	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	0.34	1	mA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	0.67	0.96	1.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	1	0.96       1.3         1.47       2.1         1.6       2.3         2.04       2.8         1.21       1.8         1.82       2.8         1.97       3.1         2.5       3.9         1.46       3.65         99       139         45.3       63.4         16.1       24.2         11.2       22.4         6978       9769         1244       1742         269       592         36.3       -         42.5       -         51.8       -         30.7       -         0.8       1.2         38.7       -         38.8       -	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	1.1	1.6	2.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	1.4	2.04	2.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	0.85	1.21	1.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	1.26	1.82	2.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	1.4	1.97	3.1	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	1.76	2.5	3.9	mΩ
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.58	1.46	3.65	mΩ
Dynamic cl	naracteristics					
$Q_{G(tot)}$	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14	-	99	139	nC
		$I_D$ = 25 A; $V_{DS}$ = 20 V; $V_{GS}$ = 10 V; Fig. 13; Fig. 14 $I_D$ = 25 A; $V_{DS}$ = 20 V; $V_{GS}$ = 4.5 V; Fig. 13; Fig. 14 $V_{DS}$ = 25 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	45.3	63.4	nC
Q <sub>GS</sub>	gate-source charge		-	16.1	24.2	nC
Q <sub>GD</sub>	gate-drain charge		-	11.2	22.4	nC
C <sub>iss</sub>	input capacitance		-	6978	9769	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	1244	1742	pF
C <sub>rss</sub>	reverse transfer capacitance		-	269	592	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 4.5 \text{ V};$	-	36.3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	42.5	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	51.8	-	ns
t <sub>f</sub>	fall time	1	-	30.7	-	ns
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	38.7	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	38.8	-	nC
S	softness factor	†	-	0.8	-	
		$I_S$ = 25 A; $dI_S/dt$ = -500 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_i$ = 25 °C; Fig. 17	-	0.72	-	

### N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56

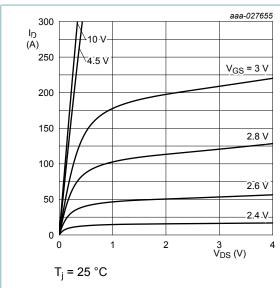


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

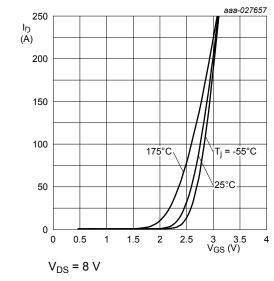


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

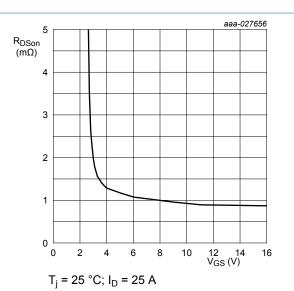


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

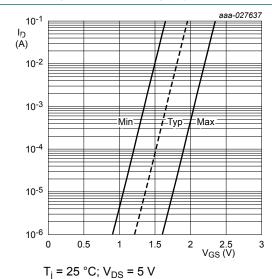


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

### N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56

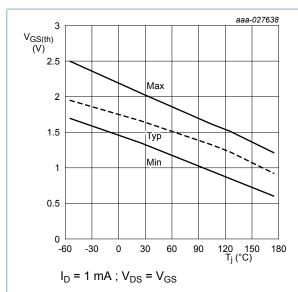


Fig. 10. Gate-source threshold voltage as a function of junction temperature

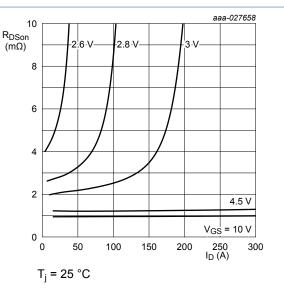


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

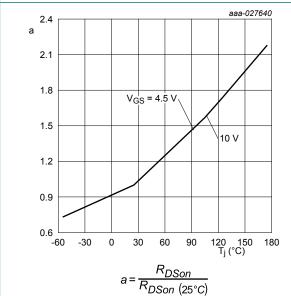


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

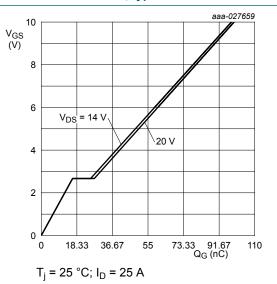


Fig. 13. Gate-source voltage as a function of gate charge; typical values

### N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56

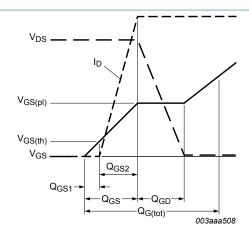
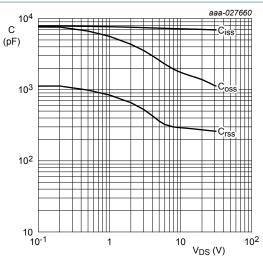


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

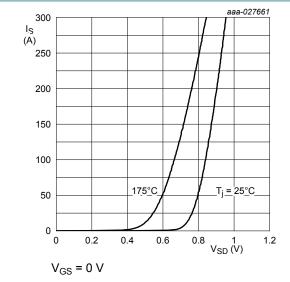
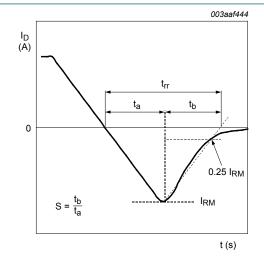


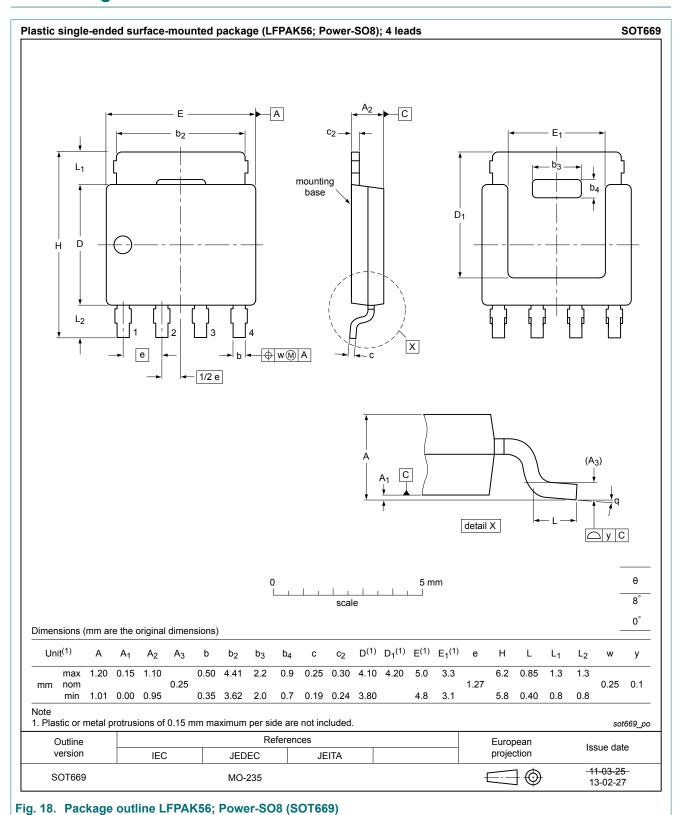
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $t_{rr} = t_a + t_b$ 

Fig. 17. Reverse recovery waveform definitions

# 11. Package outline



# 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## N-channel 40 V, 1.3 m $\Omega$ logic level MOSFET in LFPAK56

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